



# 1N6095 thru 1N6096R

## Silicon Power Schottky Diode

$V_{RRM} = 20\text{ V} - 40\text{ V}$

$I_F = 25\text{ A}$

### Features

- High Surge Capability
- Types up to 40V  $V_{RRM}$

DO-4 Package



### Maximum ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified ("R" devices have leads reversed)

Parameter	Symbol	Conditions	1N6095 (R)	1N6096 (R)	Unit
Repetitive peak reverse voltage	$V_{RRM}$		30	40	V
RMS reverse voltage	$V_{RMS}$		21	28	V
DC blocking voltage	$V_{DC}$		30	40	V
Continuous forward current	$I_F$	$T_C \leq 100\text{ °C}$	25	25	A
Surge non-repetitive forward current, Half Sine Wave	$I_{F,SM}$	$T_C = 25\text{ °C}$ , $t_p = 8.3\text{ ms}$	400	400	A
Operating temperature	$T_j$		-55 to 150	-55 to 150	°C
Storage temperature	$T_{stg}$		-55 to 175	-55 to 175	°C

### Electrical characteristics, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	1N6095 (R)	1N6096 (R)	Unit
Diode forward voltage	$V_F$	$I_F = 25\text{ A}$ , $T_j = 25\text{ °C}$	0.58	0.58	V
Reverse current	$I_R$	$V_R = 20\text{ V}$ , $T_j = 25\text{ °C}$	2	2	mA
		$V_R = 20\text{ V}$ , $T_j = 125\text{ °C}$	250	250	

### Thermal characteristics

Parameter	Symbol	Conditions	1N6095 (R)	1N6096 (R)	Unit
Thermal resistance, junction - case	$R_{thJC}$		1.8	1.8	°C/W

